

# Experimental and numerical study of an oCVD process for the deposition of PEDOT thin films

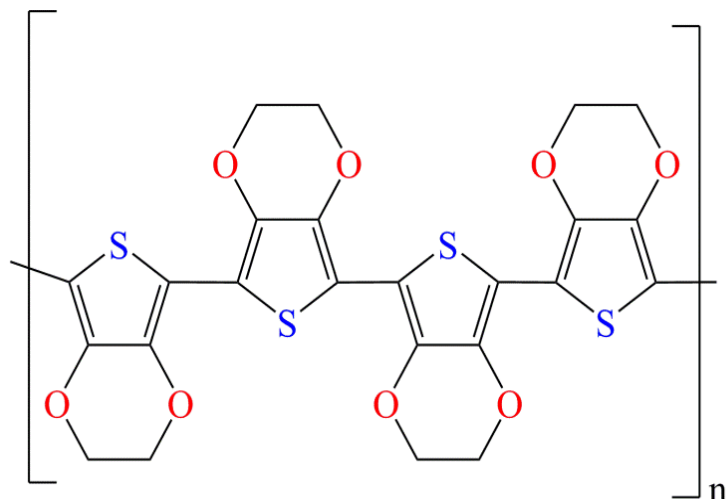
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# State-of-the-art about PEDOT thin films



**PEDOT polymer**

**Numerous applications in organic devices**

**Conductivity : 0.1 to 5000 S/cm**

## Deposition processes of PEDOT film:

- Spin-coating (aqueous suspension)
- Sequential dip-coating (liquid solution)
- Electrochemical polymerization (electrolyte)

## Drawbacks:

- ☐ High contamination with solvent residuals
- ☐ Low diffusivity in substrates with complex 3D structure
- ☐ Solvent-substrate compatibility
- ☐ Conductive substrate (Electrochemical polymerization)

**A new process by Gleason's group since 2007**

**Gas phase (CVD)**



**Oxidative chemical vapor deposition (oCVD)**

# Oxidative chemical vapor deposition (oCVD)

## Advantages:

- No contamination due to solvent
- High diffusion in gas phase under vacuum
  - Uniform concentration distribution
  - Uniform thickness
- Working at ambient temperature
  - Suitable for temperature-sensitive substrates
- Depositing on any substrate
  - Porous materials, fibers, 3D objects, paper, membrane, textile...

## However:

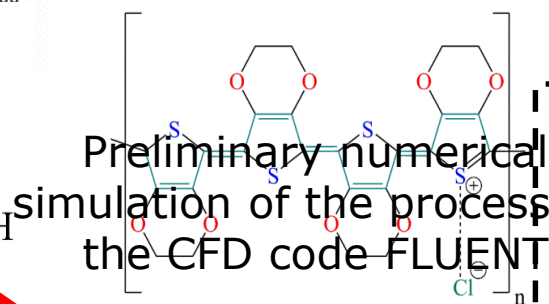
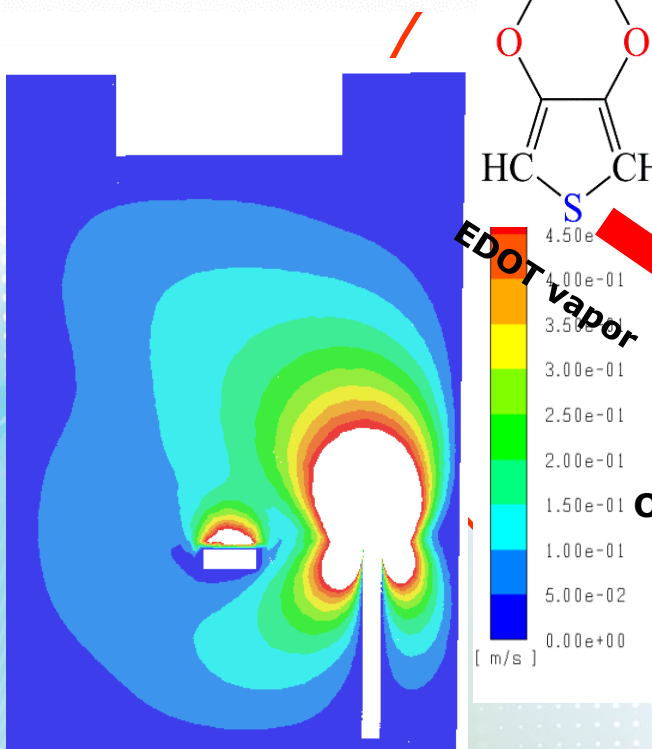
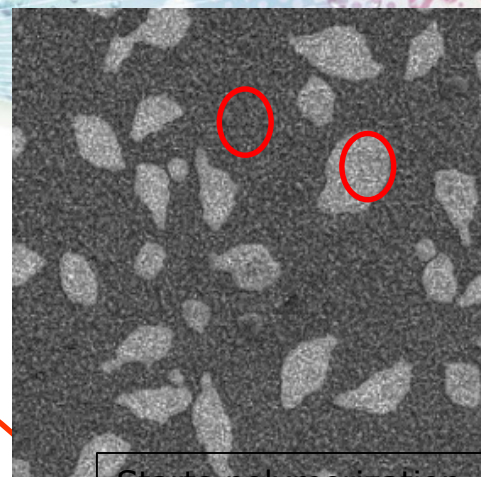
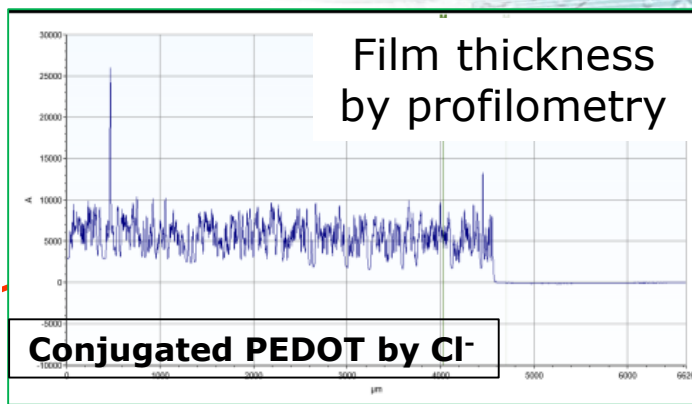
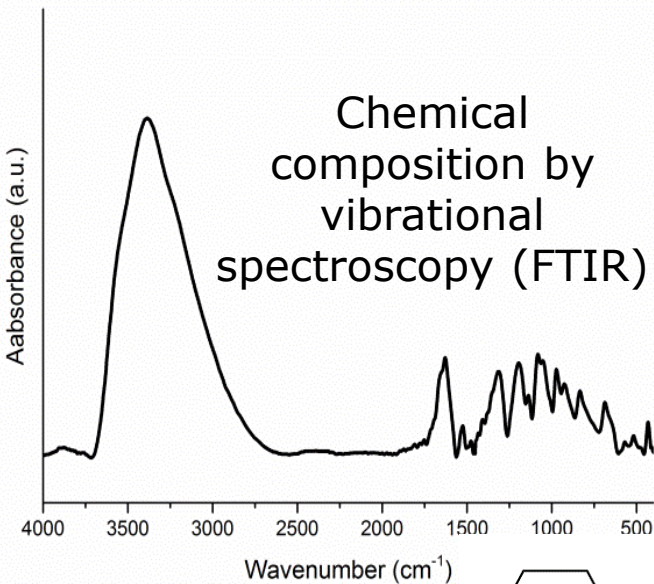
- The links between process parameters and film properties are not well understood.
- A post-deposition rinsing is necessary to remove by-products and unreacted materials to improve conductivity.

**Dedicated studies are necessary  
targeting process optimization for the  
production of highly conductive  
PEDOT**



## **Aim of the project**

Combine experimental and numerical studies to correlate film properties to deposition conditions



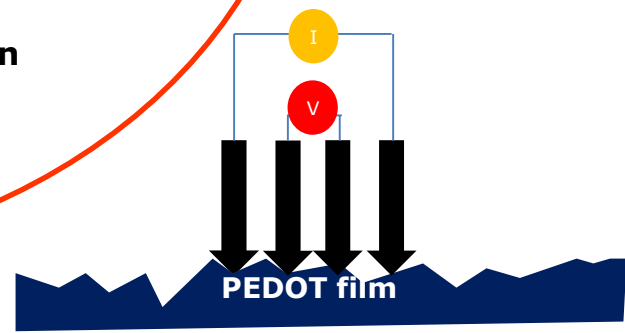
Oxidative chemical vapor deposition (oCVD)

morphology by SEM

Starts polymerization Surface

Dopes polymer

Electrical conductivity by 4-point probe

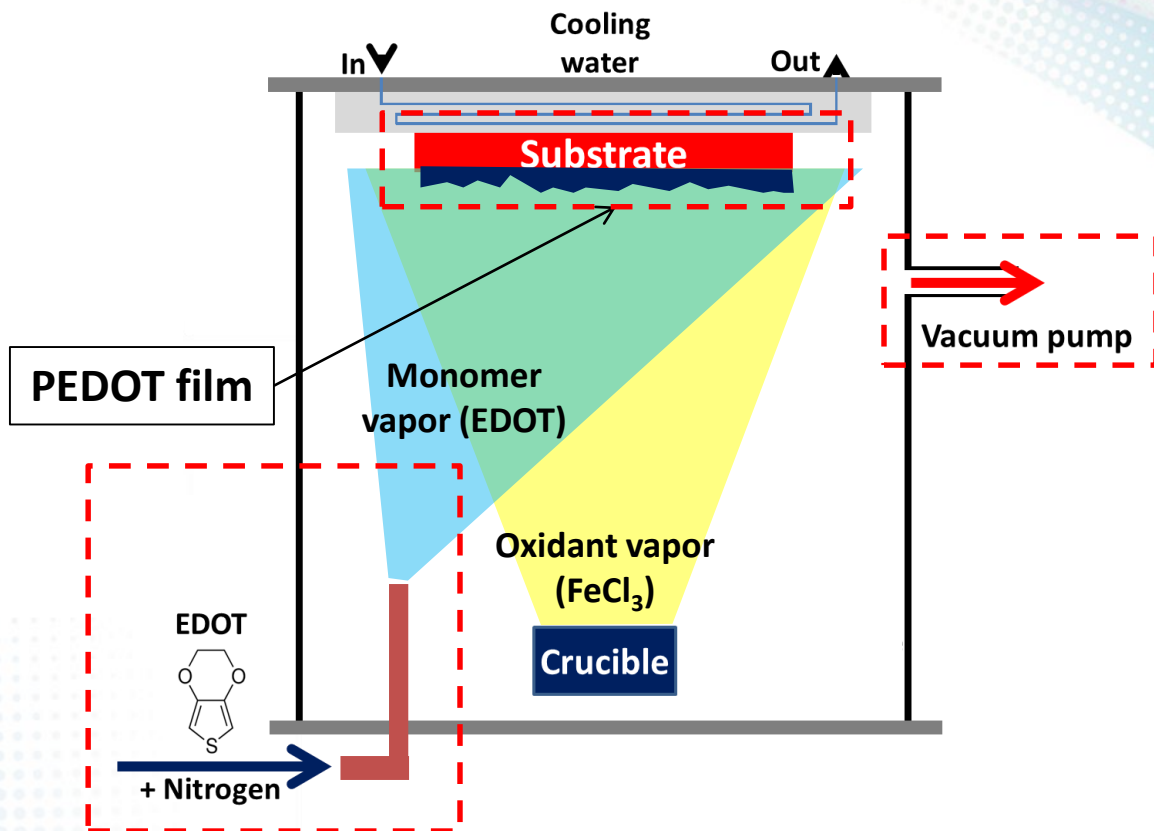


# Schematic view of the oCVD reactor

## Deposition conditions

- Deposition duration: 30 min
  - Total pressure: 100 mTorr
  - Substrate temperature kept at 20°C
  - Constant EDOT flow rate through a jar kept at 70°C
  - Constant Nitrogen flow rate
- Post treatment after deposition**
- send after the jar to carry EDOT vapor

Rinsing in MeOH and drying in air



Substrate: Silicon wafers with diameter of 10 cm

## Studying the effect of the $\text{FeCl}_3$ /EDOT ratio

### How to change this ratio?

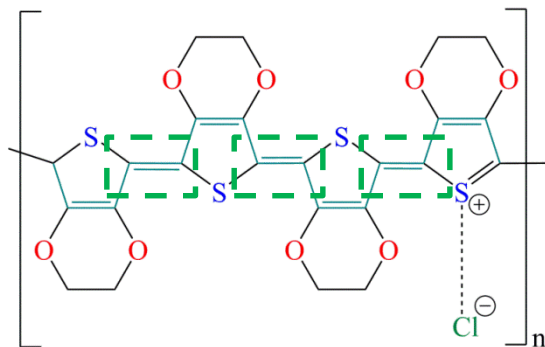
Constant EDOT flow rate, varying  $\text{FeCl}_3$  flow rate

$\text{FeCl}_3$ crucible temperature	$\text{FeCl}_3$ /EDOT inlet molar ratio
175°C	1.75
200°C	2.33
240°C	7.53

Let us go to the results...

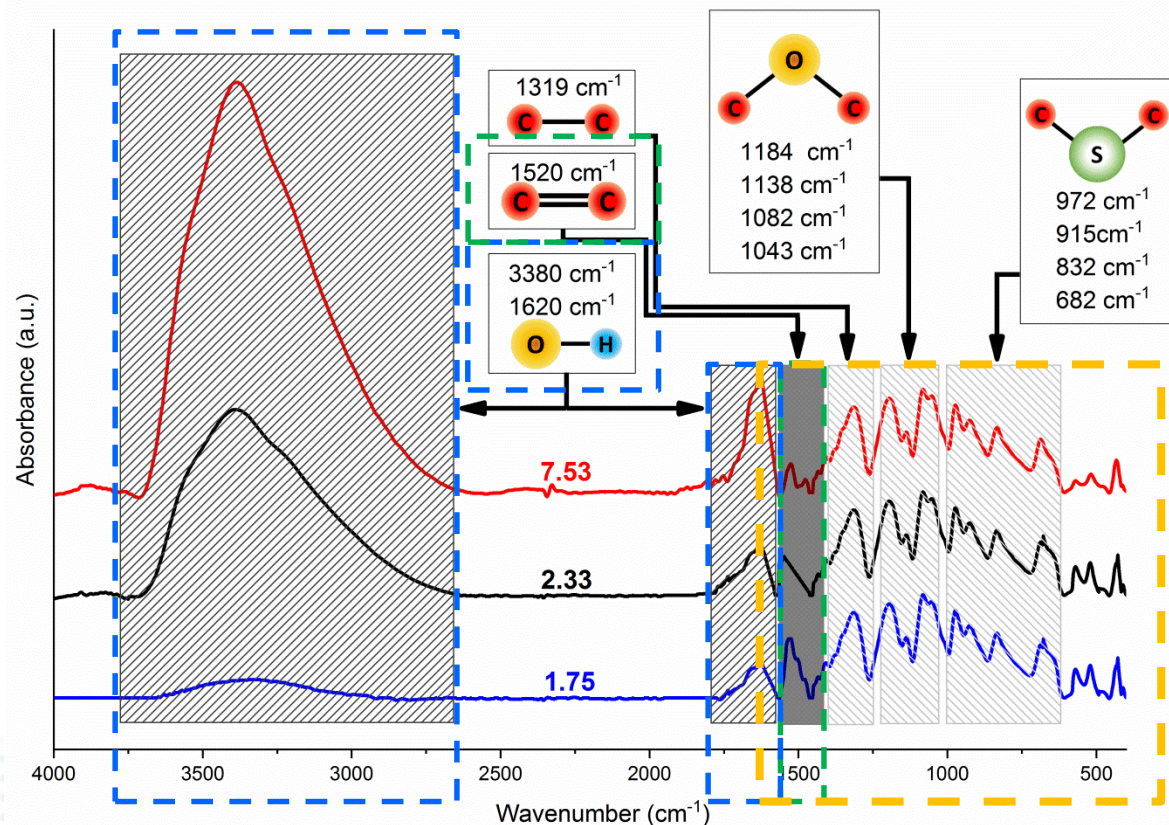


# Influence of the inlet $\text{FeCl}_3$ /EDOT ratio on vibrational spectrometry response of the films



**PEDOT polymer backbone  
(Doped with Chlorine)**

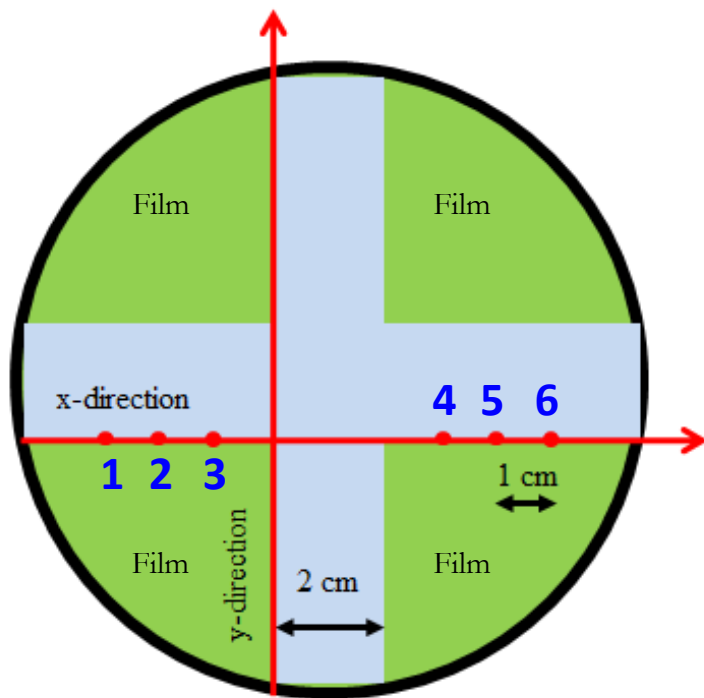
- The deposited films are PEDOT
- Hygroscopic behavior of  $\text{FeCl}_3$  or presence of iron oxides
- Increasing the  $\text{FeCl}_3$ /EDOT ratio:  
 → Higher intensity of OH peaks  
 → Lower intensity of **asymmetric stretching of C=C inter-ring bonds**, which could decrease the conductivity



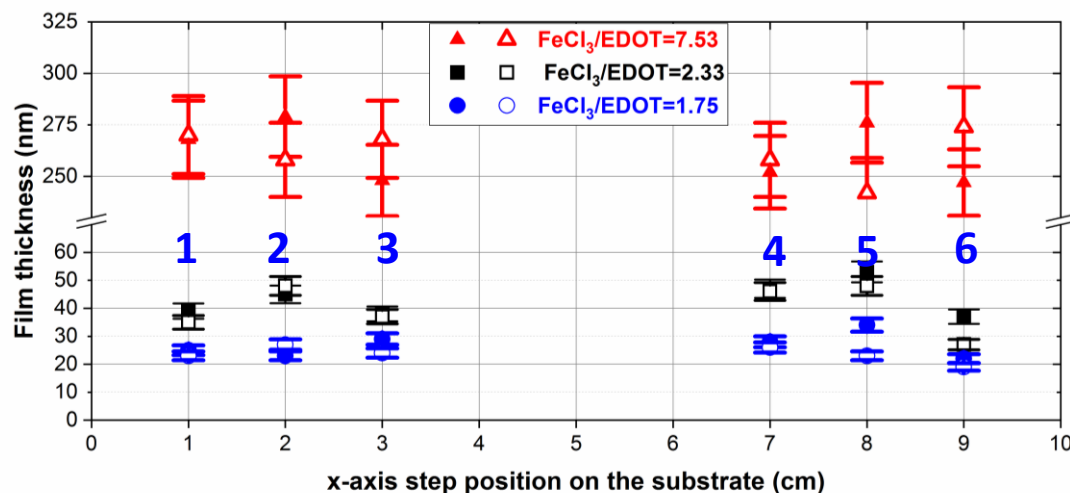
**FTIR spectra for the three  $\text{FeCl}_3$ /EDOT ratios**



# Influence of the inlet $\text{FeCl}_3$ /EDOT ratio on local film thickness (profilometry)



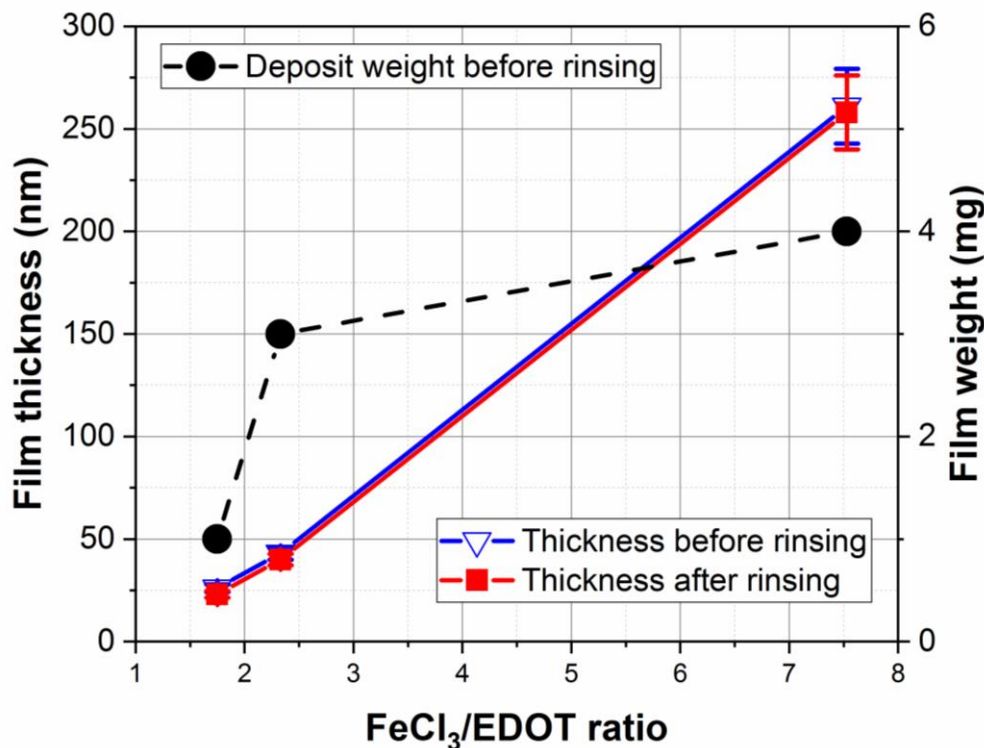
*Thickness measurement points on the silicon wafer*



*Full points: before rinsing, empty points: after rinsing*

**Uniform thickness on 10 cm silicon wafers before and after rinsing**

# Influence of the inlet $\text{FeCl}_3/\text{EDOT}$ ratio on average thickness (profilometry) and film weight

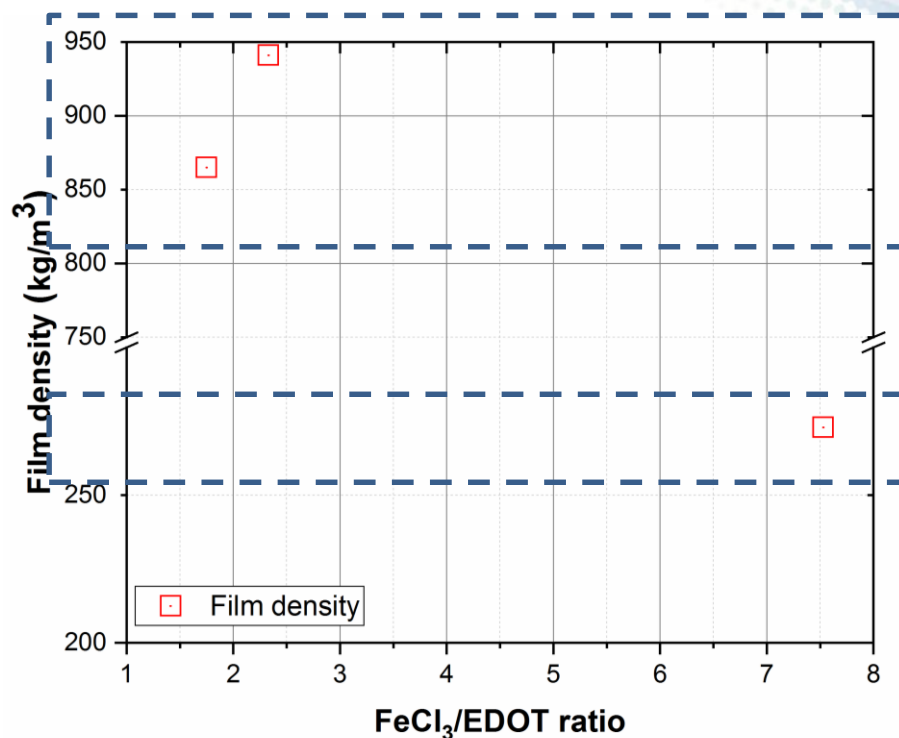


- Seemingly linear increase of the thickness with the  $\text{FeCl}_3/\text{EDOT}$  ratio.
- Rinsing with MeOH does not change the thickness
- Non-linear increase for the film weight with the  $\text{FeCl}_3/\text{EDOT}$  ratio, probably due to changes in film composition or porosity.

# Influence of the inlet $\text{FeCl}_3$ /EDOT ratio on the film apparent density (profilometry and deposit weight)

$$\rho = \frac{\text{deposit mass}}{\text{film thickness} \times \text{coated area}}$$

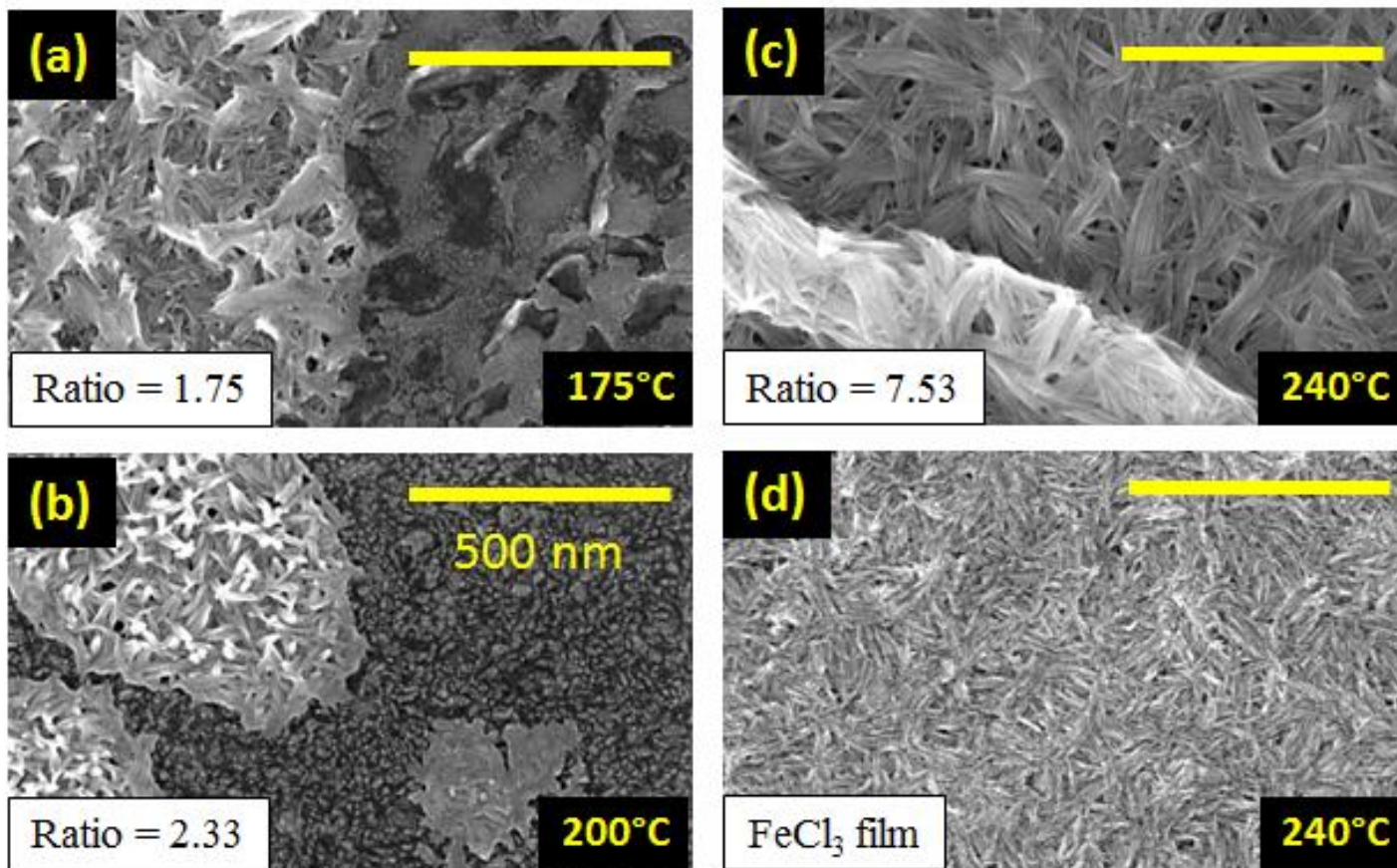
**Significant change in apparent density for the highest  $\text{FeCl}_3$ /EDOT ratio**



**→ As the three films contain PEDOT, the different evolution for thickness and deposited mass probably comes from film porosity variation.**



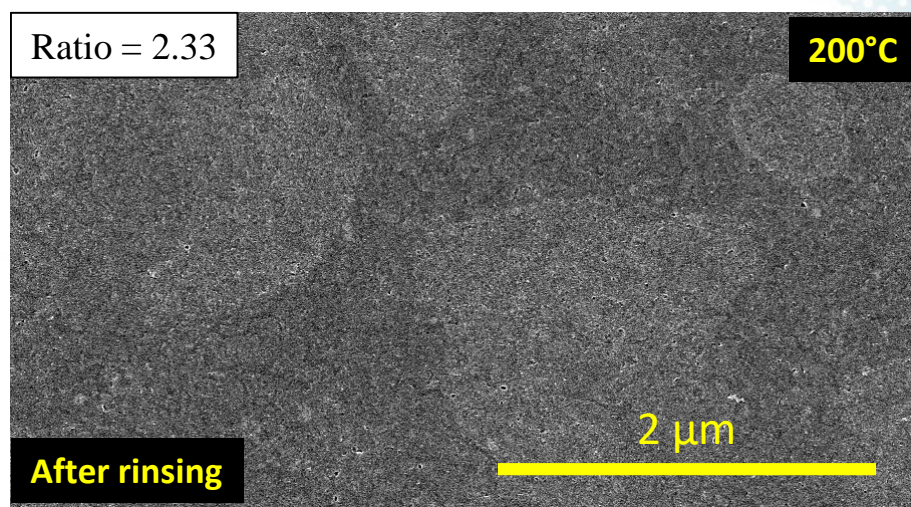
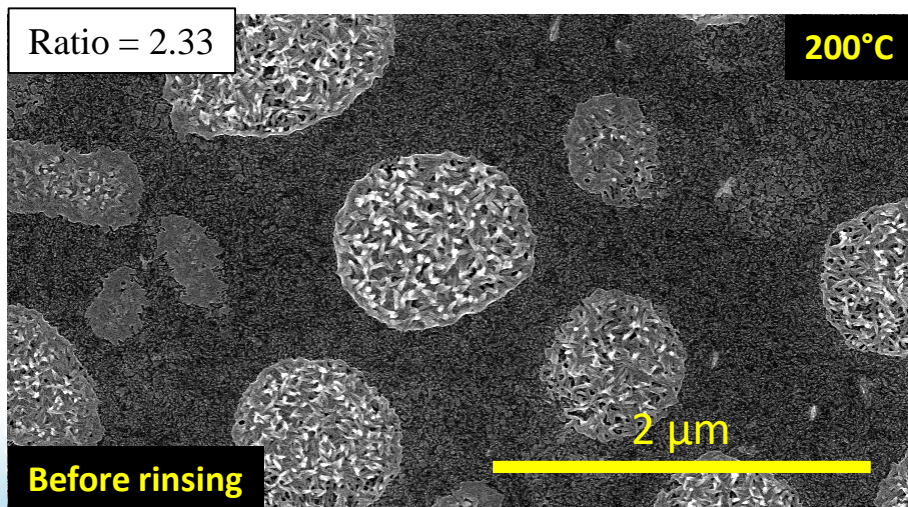
# Influence of the inlet $\text{FeCl}_3$ /EDOT ratio on the film morphology before rinsing (SEM)



- Porous films
- Two different morphologies depending on the  $\text{FeCl}_3$ /EDOT ratio
- For the highest ratio: deposit morphology close to that of sublimated  $\text{FeCl}_3$
- Zones of different compositions measured by EDX

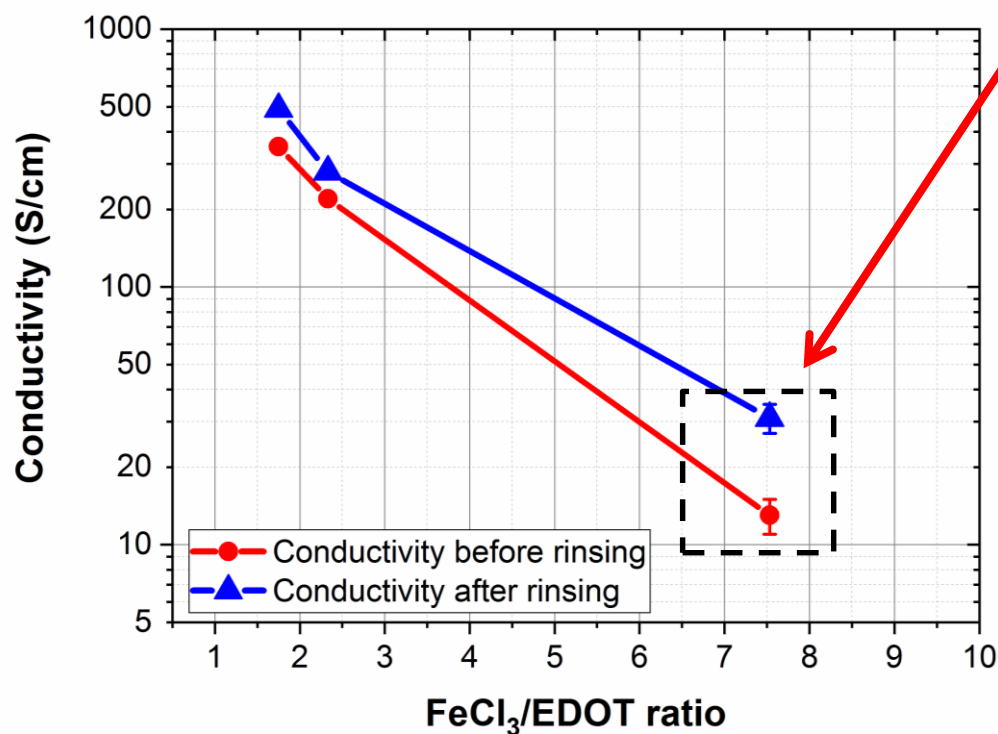


# Influence of the inlet $\text{FeCl}_3/\text{EDOT}$ ratio on the film morphology (SEM) before and after rinsing



- **Bright zones disappeared after rinsing**
- **Rinsing in MeOH removes impurities**

# Influence of the inlet $\text{FeCl}_3/\text{EDOT}$ ratio on the film electrical conductivity (4-point probe)



One order of magnitude decrease

- Decrease of the conductivity when the  $\text{FeCl}_3/\text{EDOT}$  increases.
  - Conjugation length decreases
- Rinsing with MeOH improves the conductivity slightly.

Im and Gleason, (2007)  
 3 sccm EDOT and 320°C for  
 $\text{FeCl}_3$   
 at  $T_{\text{sub}} = 20^\circ\text{C}$ : 0.05 S/cm

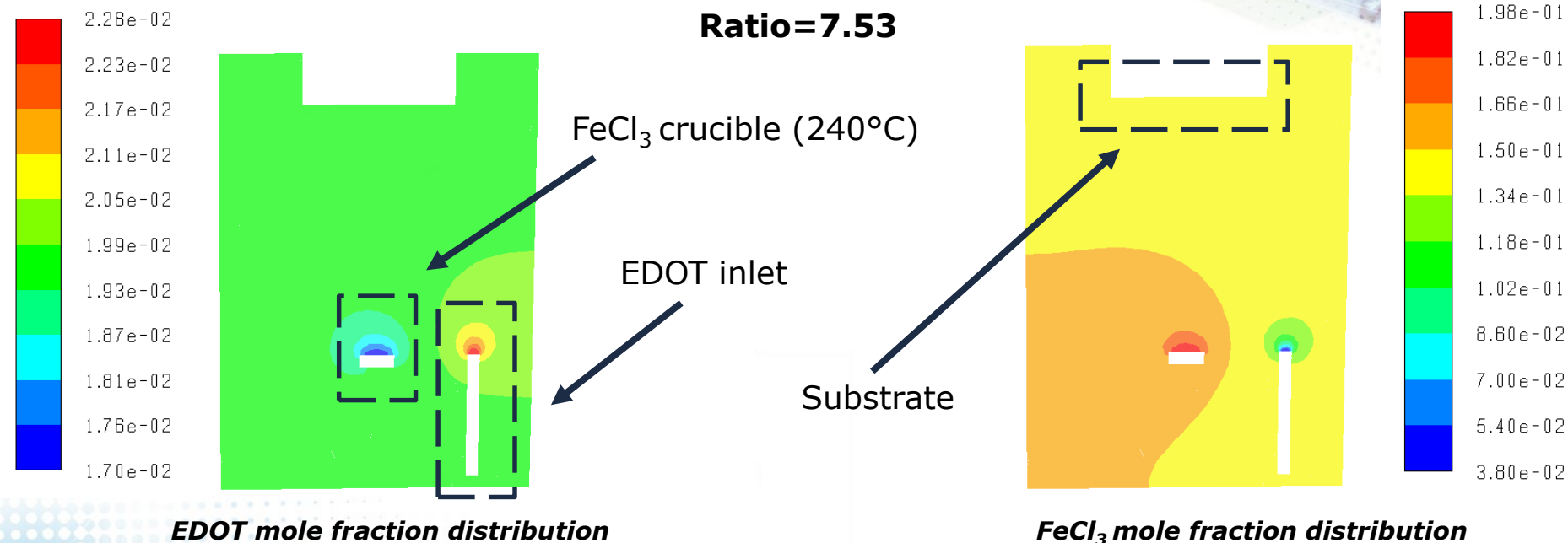
In accordance with FTIR observations



# Simulation results

## Vertical cross view of the reactor

(Simulation results without considering surface reaction)



- Uniform concentration all over the reactor for both EDOT and FeCl<sub>3</sub>, due to high gas diffusion coefficients

**In accordance with experimental observation of uniform film thickness**

## Simulation results

### Influence of the inlet $\text{FeCl}_3$ /EDOT ratio on flux near the substrate (Preliminary simulation results)

Inlet $\text{FeCl}_3$ /EDOT ratio	Experimental deposition rate/Calculated total reactant flux (%)
1.75	1.07
2.33	1.33
7.53	1.20

- Only one percent of the flux of reactants reaching the substrate is responsible for the deposit → strong kinetic limitation.

# Conclusions

- Deposition of PEDOT thin film of uniform thickness on 10 cm Si substrates at ambient temperature
- Sending more  $\text{FeCl}_3$  into the reactor:
  - Increases the film thickness
  - Changes in a coherent way the film morphology, porosity and composition
  - Decrease the amounts of  $\text{C}=\text{C}$  bonds and logically the conductivity
- Rinsing with MeOH
  - Slightly improves the conductivity
- Simulation results
  - Uniform concentration and weak contribution of reactants to the deposition
  - Strong kinetic limitation

**The  $\text{FeCl}_3$ /EDOT ratio and more largely all the deposition parameters must be controlled to produce highly conductive PEDOT.**



# Perspectives

Optimize all contributing parameters in the deposition process to produce PEDOT with the best physical properties (in progress)

Measure in real time the deposition rate with an *in situ* quartz microbalance (in progress)

Develop apparent kinetic laws for reaction rates to be implemented in the reactor model (in progress)

Study films on complex substrates for applications in organic electronics

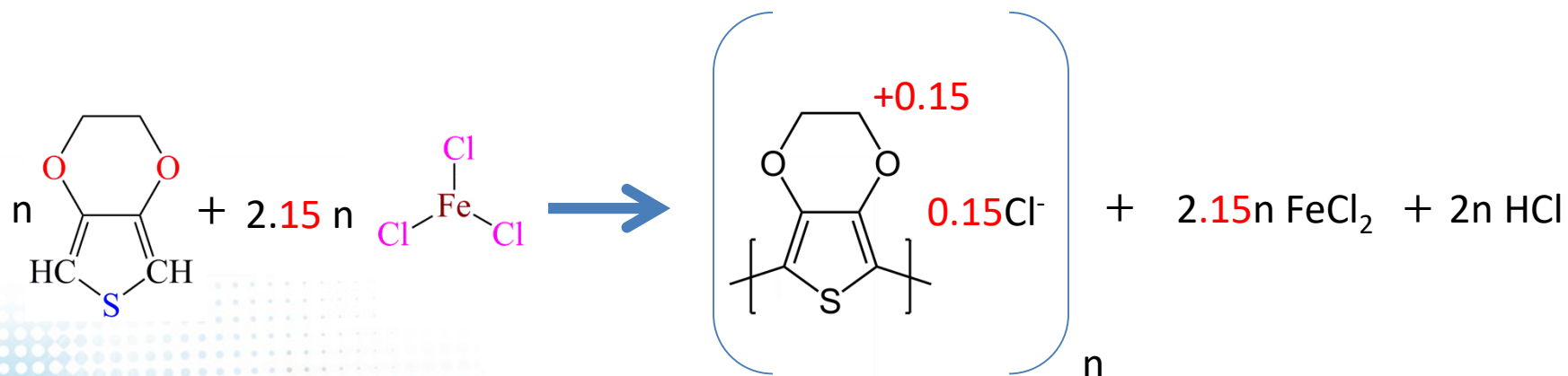
# Thank you!







Our proposition based on other polymers:

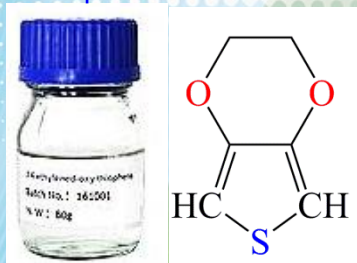
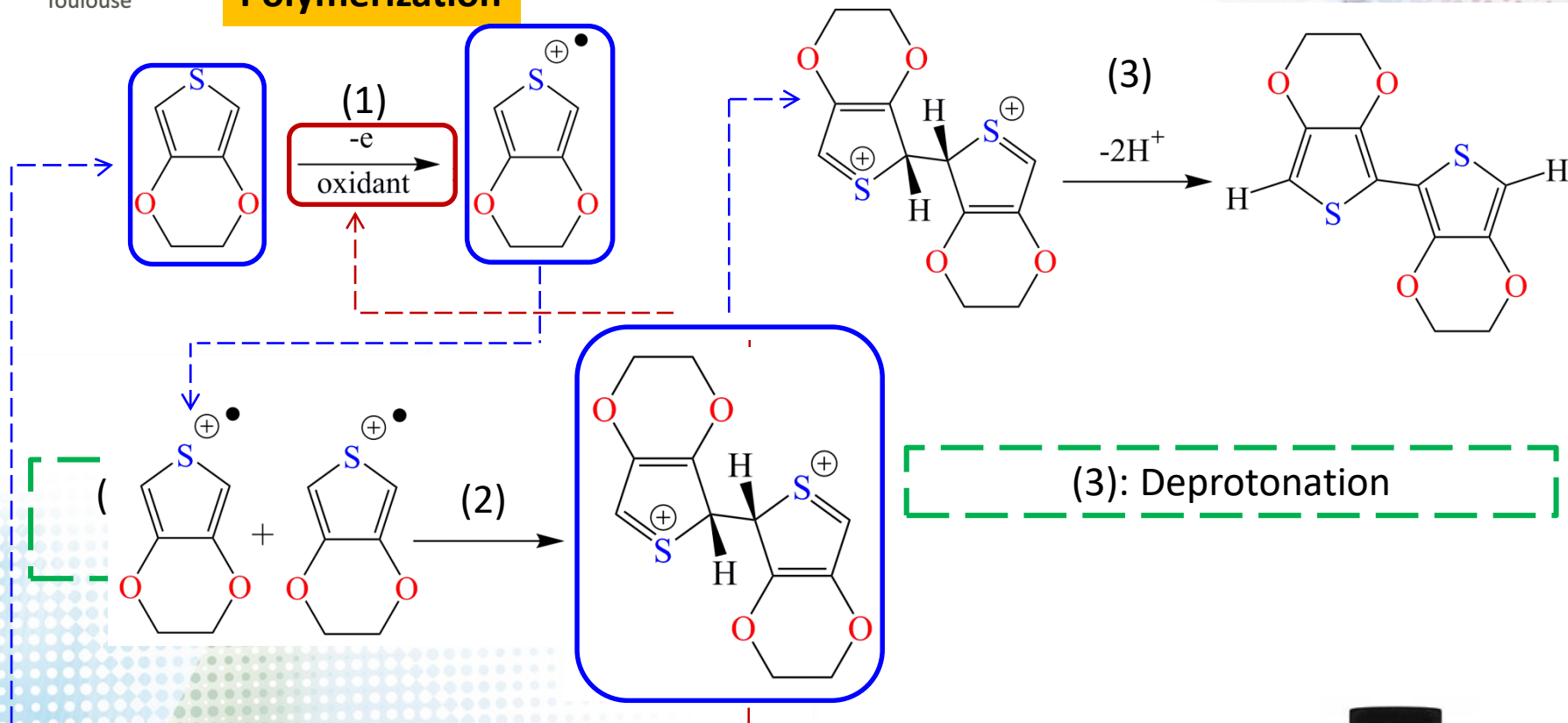


With 0.15 as the ratio of Cl/S, we are considering that for each 7 EDOT units, there is one Cl with negative charge. Therefore, the

$$M_w = 2 + (0.15 \times 35 + 140) = 147.25$$

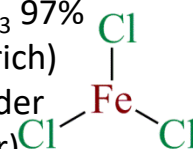
# Proposed polymerization mechanism in the literature for PEDOT by oCVD [6]

## Polymerization



Oxidant:  $\text{FeCl}_3$  97%  
(Sigma-Aldrich)

Black powder  
(Insulator)

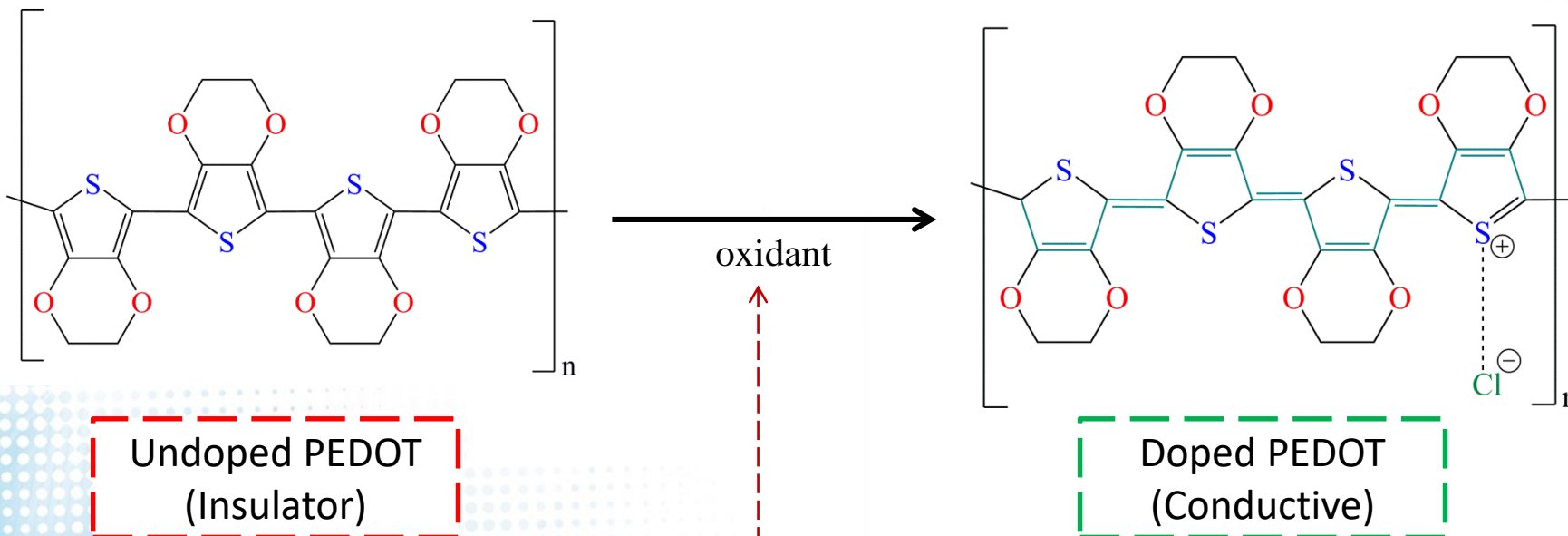




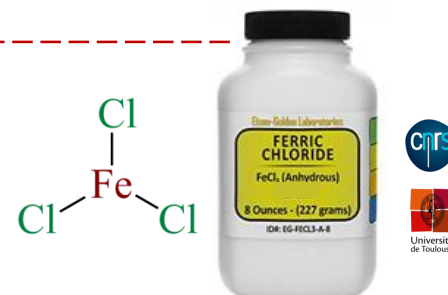
# Proposed polymerization mechanism in the literature for PEDOT by oCVD [6]

## Doping

### (4): Chlorine doping of polymer backbone

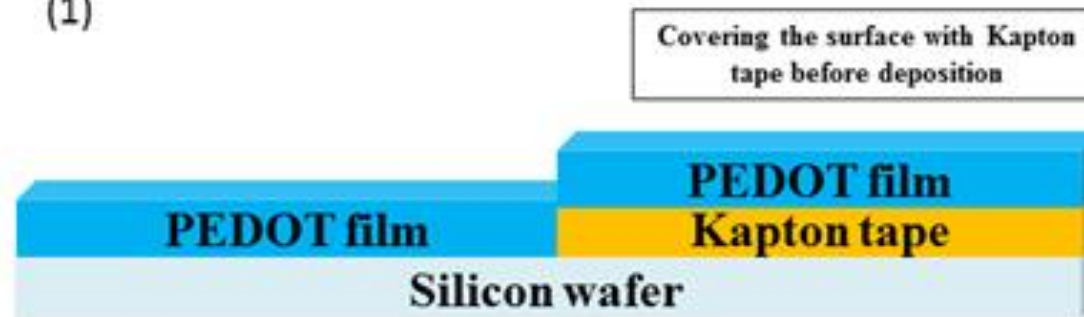


- Presence of Chlorine in the backbone
- Presence of C=C inter-ring bond in the backbone (conjugation and conductivity)
- Removal of C-H bond in the thiophene ring due to the polymerization

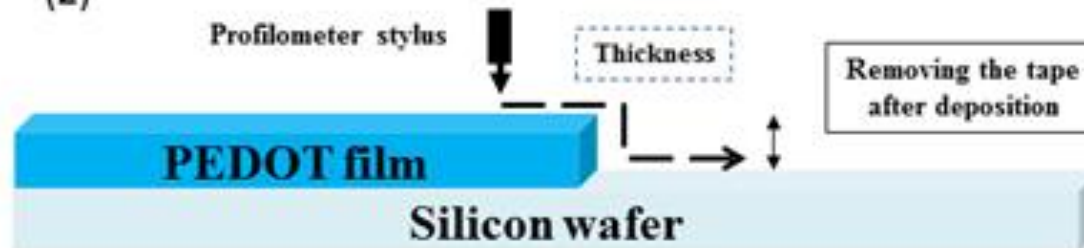


## Influence of inlet $\text{FeCl}_3$ /EDOT ratio

(1)

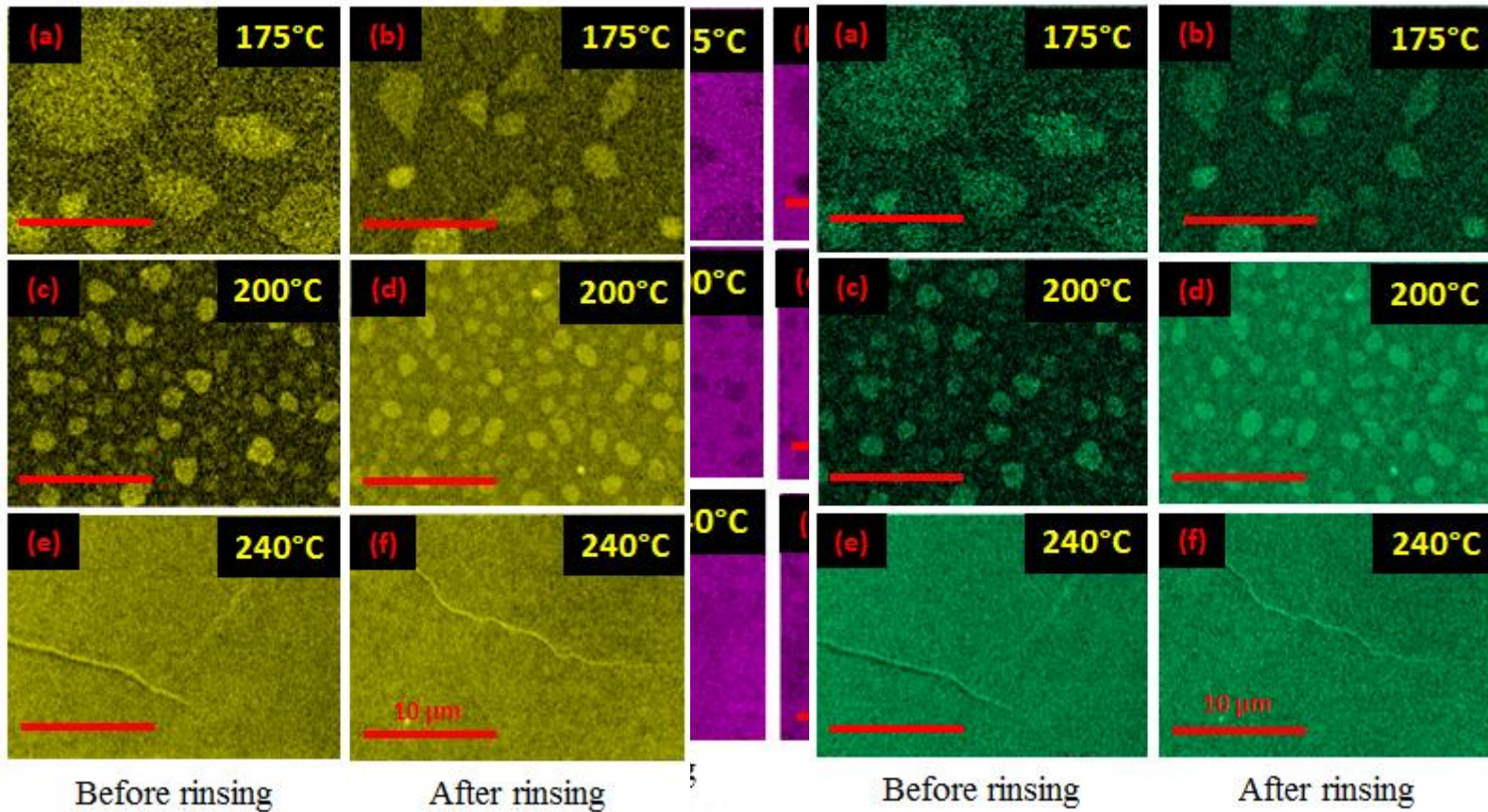


(2)



Thickness measurement procedure on the substrate

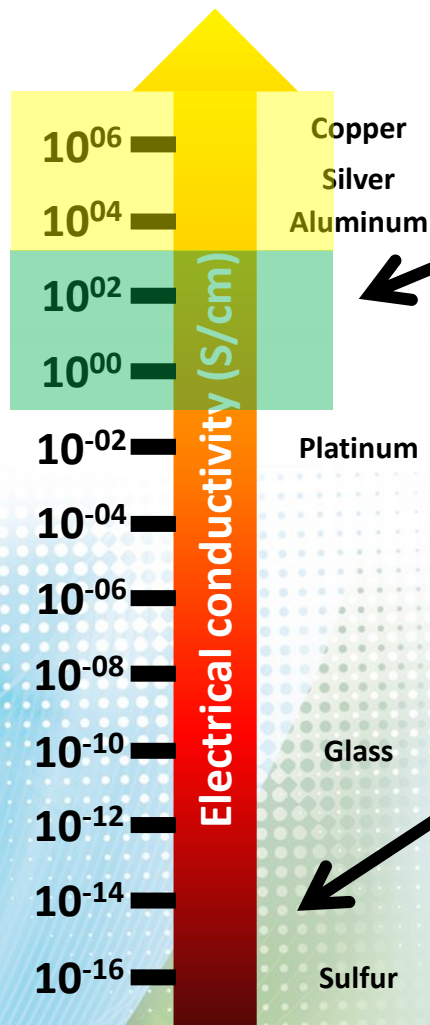




EDX analysis of surface for Iron



# CONDUCTIVE POLYMERS



Conductive polymers are organic polymers (containing Carbon) that conduct electricity.

Such compounds may have metallic conductivity ( $10^6$  S/cm) or can be semiconductors ( $10^{-3}$  to  $10^4$  S/cm).

Their electrical properties can be fine-tuned during the synthesis process.

Doped  
(Semi conductors:  $10^{-1}$  to  $10^3$  S/cm)



Neutral polymers  
Undoped  
(Insulators:  $10^{-14}$  S/cm)

# Why conductive polymers and not metals?

## Polymeric properties

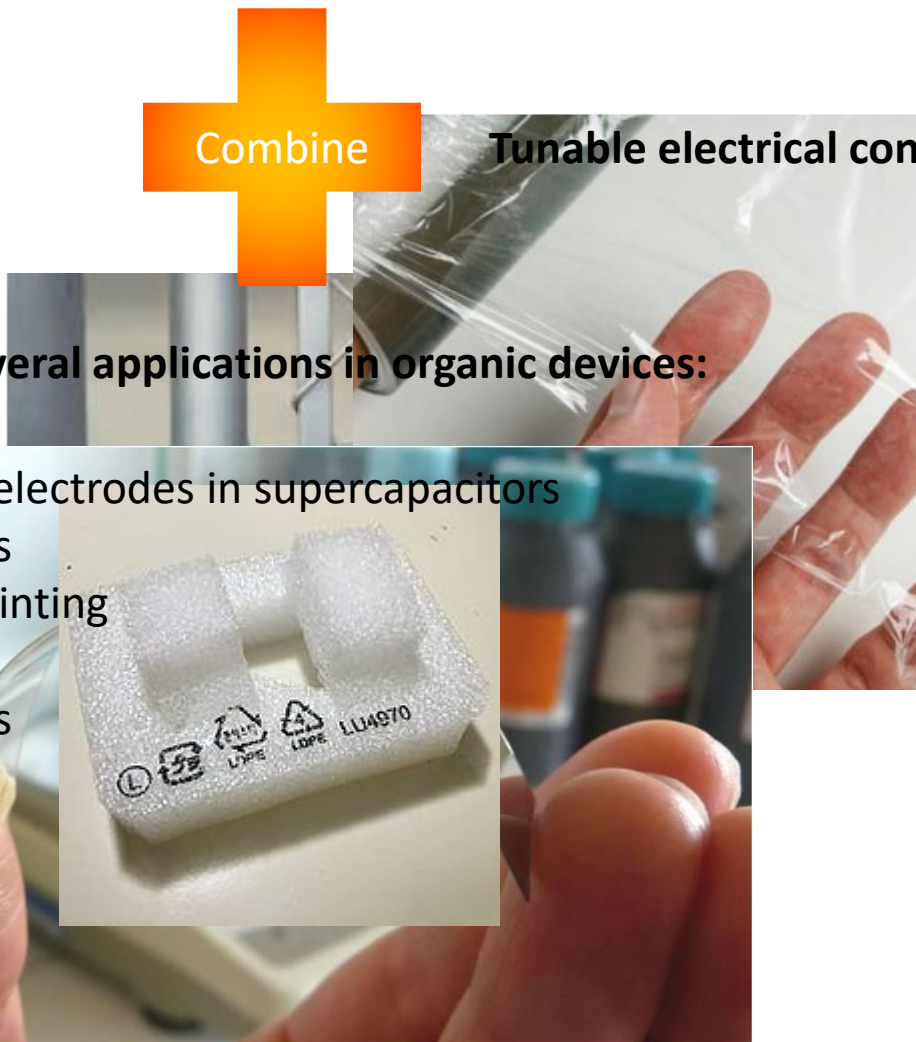
- Optical transparency
- Low density
- Corrosion resistance
- Flexibility

Combine

Tunable electrical conductivity

Lead to several applications in organic devices:

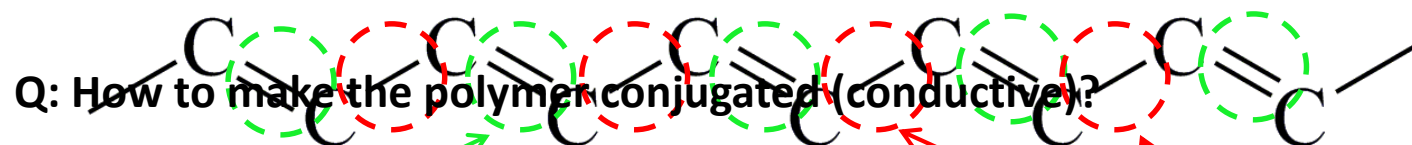
- Flexible, lightweight electrodes in supercapacitors
- Hydrophobic surfaces
- Conductive ink for printing
- P-layer in solar cells
- Conductive adhesives
- Functional textiles



## Theory:

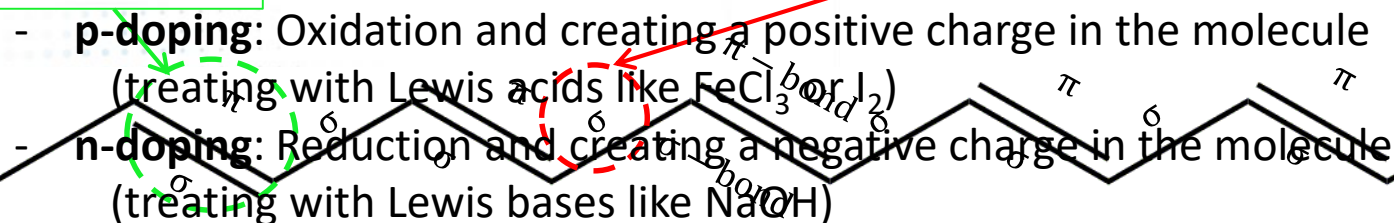
Electrical conductivity in polymers comes from the presence of **conjugated bond structure** through **doping** that permits  **$\pi$ -orbital overlap** along the **alternating double and single-bonds** in the polymer backbone.

Q: How to make the polymer conjugated (conductive)?



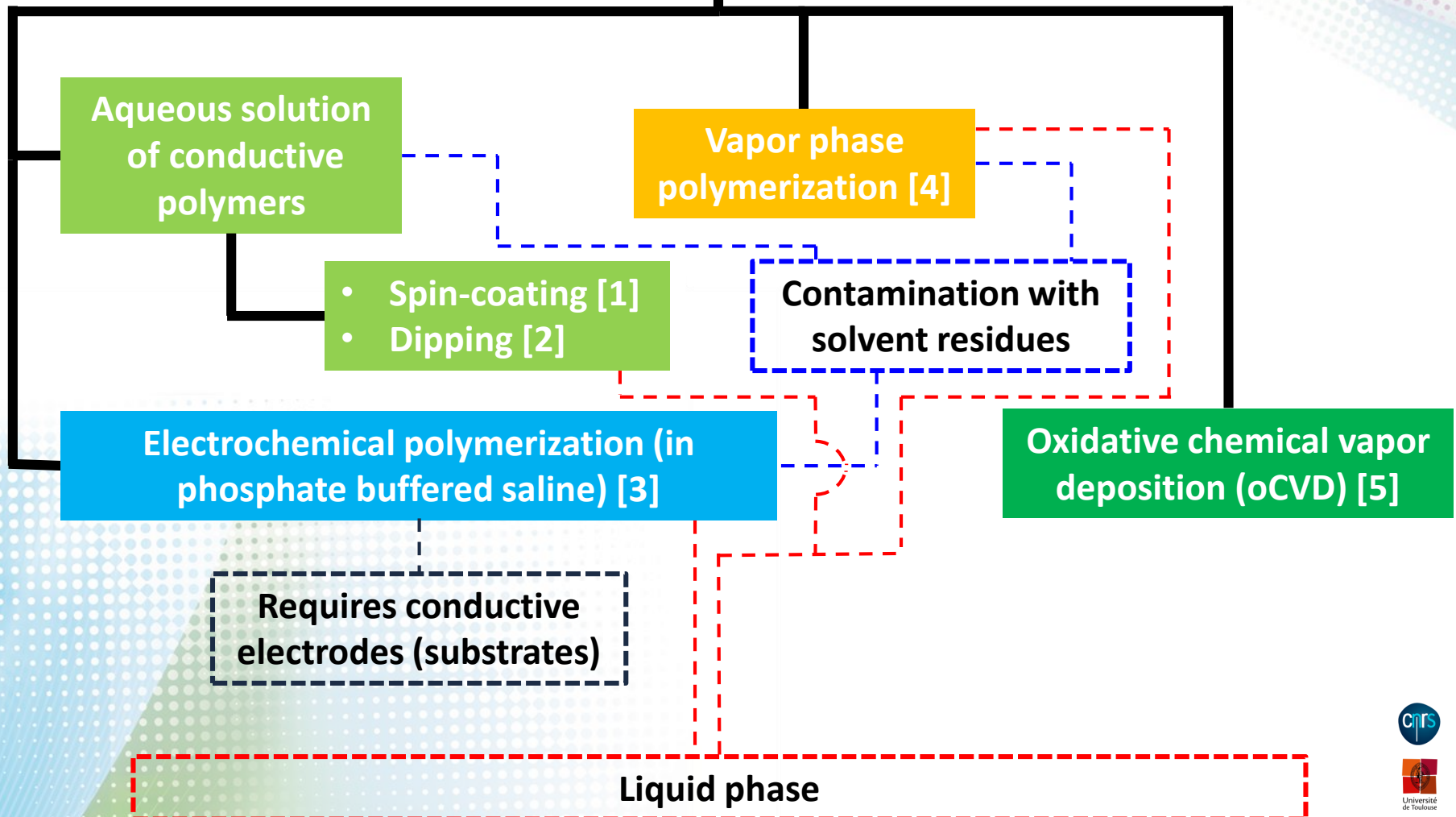
A: By creating bond conjugation through doping (two types) bond

### Double bond

- **p-doping:** Oxidation and creating a positive charge in the molecule (treating with Lewis acids like  $\text{FeCl}_3$  or  $\text{I}_2$ )
  - **n-doping:** Reduction and creating a negative charge in the molecule (treating with Lewis bases like  $\text{NaOH}$ )
- 



## How to deposit a layer of PEDOT on a surface?



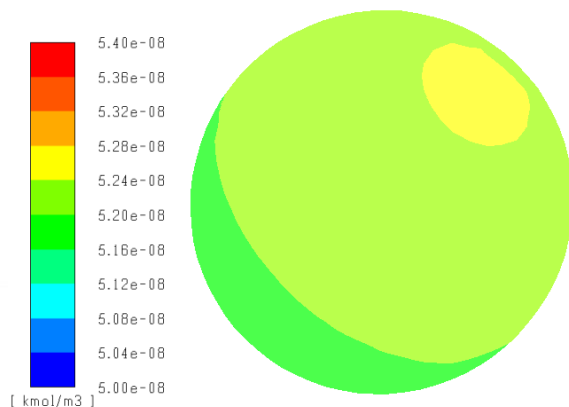
# Influence of the inlet $\text{FeCl}_3$ /EDOT ratio on flux near substrate (Preliminary simulation results)

Inlet $\text{FeCl}_3$ /EDOT ratio	Simulations by FLUENT		Sum of $\text{EDOT} + \text{FeCl}_3$ fluxes near substrate ( $\text{kg/m}^2.\text{s}$ )	Experiments Experimental deposition rate ( $\text{kg/m}^2.\text{s}$ )	Experimental deposition rate/Calculated total reactant flux (%)
	$\text{FeCl}_3$	EDOT			
1.75	Increases with the ratio	Constant	1.17E-06	1.25E-08	1.07
2.33			1.89E-06	2.52E-08	1.33
7.53			3.30E-06	3.97E-08	1.20

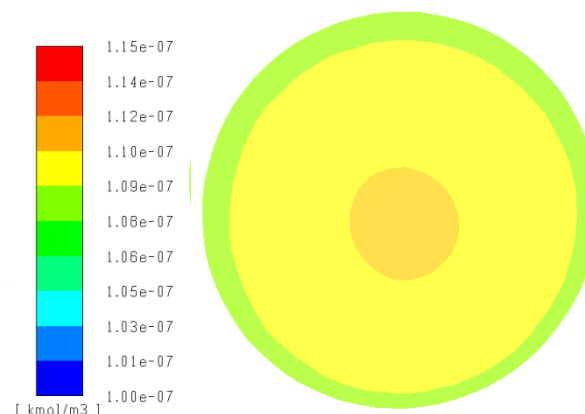
- Only one percent of the flux of reactants reaching the substrate is responsible for the deposit → strong kinetic limitation.
- The deposition rate is clearly dependent of the  $\text{FeCl}_3$  flux toward the substrate (limiting reactant).

## Vertical cross view of the reactor (Simulation results without considering surface reaction)

Ratio=7.53



**EDOT concentration distribution**



**FeCl<sub>3</sub> concentration distribution**

Less than 3% variation over substrate

- Uniform concentration all over the reactor for both EDOT and FeCl<sub>3</sub>, due to high diffusion coefficients

**In accordance with experimental observation of uniform film thickness**